



60V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
60V	$9.5 \text{m}\Omega @ V_{GS} = 10V$	54.1A
	$13.3 \text{m}\Omega$ @ $V_{GS} = 4.5 \text{V}$	45.7A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

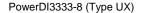
- Motor Control
- DC-DC Converters
- Power Management

Features and Benefits

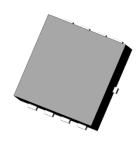
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable And Robust End Application
- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

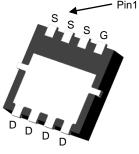
Mechanical Data

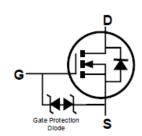
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.072 grams (Approximate)











Top View

Bottom View

Equivalent Circuit

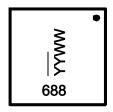
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT68M8LFV-7	PowerDI3333-8 (Type UX)	2000/Tape & Reel
DMT68M8LFV-13	PowerDI3333-8 (Type UX)	3000/Tape & Reel

es: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- <1000ppm antimony compounds.</p>
 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



688= Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	60	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current (Note 6) V _{GS} = 10V	$T_C = +25$ °C $T_C = +70$ °C	I _D	54.1 43.3	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	210	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	50	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	210	Α	
Avalanche Current, L = 0.1mH	I _{AS}	28	Α	
Avalanche Energy, L = 0.1mH	E _{AS}	39	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{ heta JA}$	47	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	P _D	41.7	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	3	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

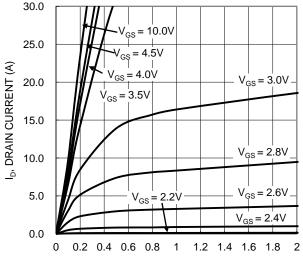
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		1	6.6	9.5	mΩ	$V_{GS} = 10V, I_D = 13.5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		9.1	13.3	11122	$V_{GS} = 4.5V, I_D = 11.5A$	
Diode Forward Voltage	V_{SD}	_	8.0	1.2	V	$V_{GS} = 0V, I_S = 13.5A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	l	2078	l	рF	.,	
Output Capacitance	Coss	l	605	l	рF	$V_{DS} = 30V, V_{GS} = 0V,$ - f = 1MHz	
Reverse Transfer Capacitance	C_{rss}		44	-	рF	1 = 1101112	
Gate Resistance	R_g	l	1.71		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Q_g		30	-	nC		
Total Gate Charge (V _{GS} = 4.5V)	Q_g		14.4	-	nC	1,, 20,4, 20,4	
Gate-Source Charge	Q_{gs}	_	4.1	_	nC	$V_{DD} = 30V, I_D = 20A$	
Gate-Drain Charge	Q_{gd}	_	6.7	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	5.2	_	ns		
Turn-On Rise Time	t _R	_	9.6	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 20A, R_{g} = 3.3\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	_	20.5	_	ns		
Turn-Off Fall Time	t _F		8.9	_	ns		
Body Diode Reverse Recovery Time	t _{RR}		32.5	_	ns	1 20A di/dt 100A/vo	
Body Diode Reverse Recovery Charge	Q_{RR}	_	22.8	_	nC	$I_F = 20A$, di/dt = 100A/ μ s	

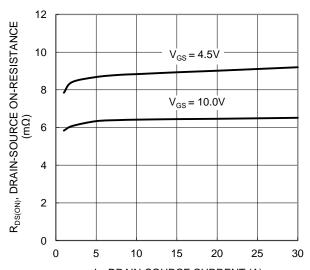
Note:

- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad)
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 1.Typical Output Characteristic



I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

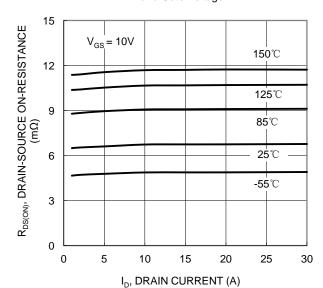


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

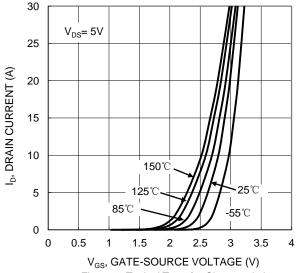


Figure 2. Typical Transfer Characteristic

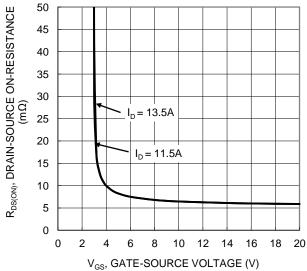


Figure 4. Typical Transfer Characteristic

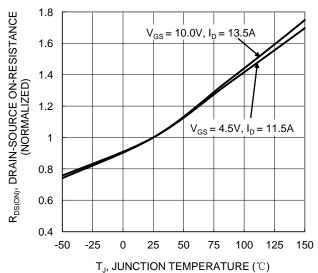
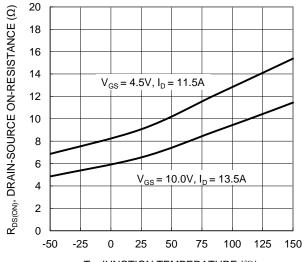
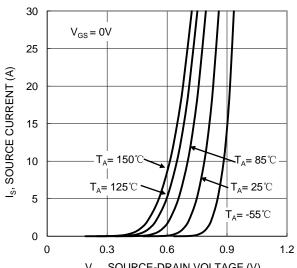


Figure 6. On-Resistance Variation with Temperature





 T_J , JUNCTION TEMPERATURE ($^{\circ}$ C) Figure 7. On-Resistance Variation with Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

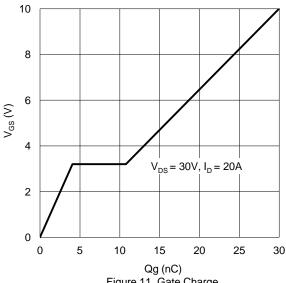
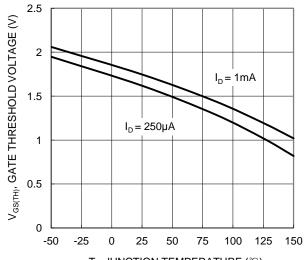
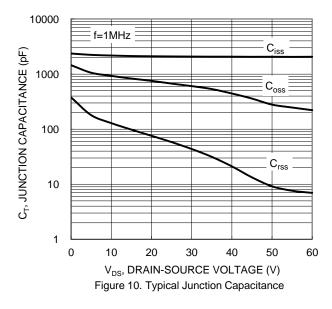


Figure 11. Gate Charge



 T_J , JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs. JunctionTemperature



1000 100 ID, DRAIN CURRENT (A) 10 1 P_w=10ms T_{J(MAX)}=150°C T_C=25 ℃ $P_W = 100 ms$ Single Pulse DUT on infinite 0.1 heatsink V_{GS}=10V 0.01 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



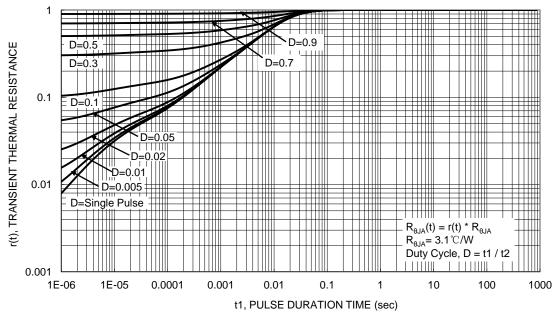


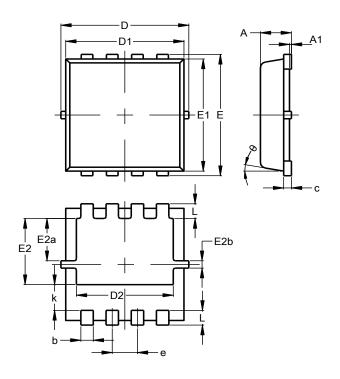
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

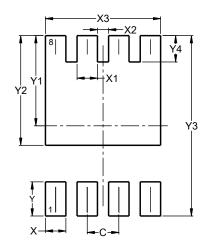


PowerDI3333-8 (Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
е	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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